

Formation of Wigner crystals in conducting polymer nanowires

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Abstract

The search for theoretically predicted Wigner crystal in one-dimensional (1D) wires of structurally disordered materials exhibiting properties of charge-density-waves have remained unsuccessful. Based on the results of a low temperature conductivity study we report here formation of such 1D Wigner crystal (1DW C) in polypyrrole nanowires having low electron densities. The current-voltage characteristics of all the nanowires show a 'gap' that decreases rapidly as the temperature is increased – confirming the existence of long-range electron-electron interaction in the nanowires. The measured current show power-law dependence on voltage and temperature as expected in 1DW C. A switching transition to highly conducting state has been observed above a threshold voltage, which can be tuned by changing the diameters of the nanowires and the temperature. Negative differential resistance and enhancement of noise has been observed above the threshold as expected.

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Possibilities of applications in nanotechnology has triggered extensive research activities to understand charge-conduction in quasi-1D conductors like nanowires and nanotubes where electron-electron interaction (EEI) plays a dominant role. In 1934 Eugene Wigner considered the effect of long-range EEI in metals and predicted in a seminal paper [1] possibility of formation of periodic spatial structures of electrons for very low electron density materials. It has been predicted theoretically that one dimensional Wigner crystal (1DW C) [2] formation exhibiting the characteristic of a charge density wave (CDW) may occur in nanowires of even structurally disordered materials [3]. Wigner crystal (WC) phase has been observed experimentally in two-dimensional electron system under intense magnetic field [4, 5], in surface-state electrons of superfluid helium [6], in quasi-1D organic charge transfer salt [7] and recently in inorganic chain compounds [8]. Although interesting phases like Luttinger liquid (LL) [9], which arise due to short-range EEI, has been observed in several one dimensional (1D) systems [10, 11, 12, 13], predicted formation of 1DW C in structurally disordered materials [3] has not been observed experimentally, to the best of our knowledge. Among various low-dimensional systems conducting polymer nanowires are easy-to-form quasi-1D systems to study EEI as one can tune the carrier concentration of a polymer over several orders of magnitudes by controlling doping concentration and WC formation has been predicted in conducting polymers [3, 14].

Here we report results of low temperature study of polypyrrole nanowires having diameters from 30 to 450 nm. Highly non-linear current-voltage (I-V) characteristics having $I \propto V^{1+}$ at high V and $I \propto T^{-1} V$ at low V was observed. The exponent reduces from high value ($\sim 5-7$) with increasing temperature and does not take equal value to ~ 1 , in general. A large 'gap' voltage (V_G), above which the conductance increase substantially, was observed in the low temperature I-V characteristics. The gap was found to decrease rapidly with increasing temperature and with increasing diameter. The I-V characteristics also show a switching transition to a highly conducting state above a certain threshold voltage $V_{Th} (> V_G)$. The threshold field (E_{Th}) corresponding to V_{Th} was found to depend on the diameter (d) as $E_{Th} \propto d^{-4/3}$. Current-driven I-V characteristics show negative differential resistance (NDR) at low temperature. An increase in 'noise' has been observed in the switched (highly conducting) state. All these experimental results give evidence in favor of pinned Wigner crystal formation in conducting polymer nanowires, as predicted theoretically [3].

Conducting polymer nanowires are quasi-1D systems composed of aligned polymer chains where charge carriers are created by doping. We used membrane based synthesis technique for growing polymer nanowires following same preparation technique describe earlier [15]. The average doping concentration (obtained after initial doping gradient within few hundred nanometer) can be systematically reduced by lowering the diameters of the nanowires [15]. The actual diameter of nanowires were characterized from SEM micrograph and were found to have an average diameter of 30, 50, 70, 110, 350 and 450 nm. Gold electrodes (2mm diameter) were sputter-deposited on both sides of the membrane to establish parallel connection with 10^7 nanowires (pore density of the membrane $10^9 = \text{cm}^{-2}$). The electrical measurements were carried out in a Oxford cryostat under liquid Helium environment using Keithley 2400 source-meter and 6517A electro-meter in two probe configuration (refer inset of Fig. 1 (a)) over the temperature range of 1.7 to 300 K. The consistency of the results were checked by changing the contact material, scan-speed of the bias voltage (current). Differential conductance ($dI=dV$) were obtained by numerically differentiating the I-V curves and verified by Lock-in measurements. In Fig. 1 (a) we have shown $dI=dV$ vs. V plots for 30 nm nanowires taken at various temperatures.

The conductance vs. voltage and $dI=dV$ vs. voltage data of various nanowires (refer Fig. 1 (a) and (b)) show existence of 'gap' voltage (V_G). We have measured the value of V_G by noting the change of slope from the conductance vs. voltage data for different diameter nanowires as shown in Fig. 1 (b). V_G was found to be inversely proportional to the diameter (d) of the nanowires (refer inset of Fig. 1 (b)). It is to be noted that zero-bias current and hence the conductance below the V_G increases with temperature and diameter of nanowires. The 'gap' was found to reduce rapidly with increase in temperature and vanishes at relatively high temperature that depends on the wire diameter.

Strong temperature dependence of 'gap' is a signature of electron-electron interaction [16, 17], and has been observed earlier in chains of graphitized carbon nanoparticle [18]. Temperature and diameter dependence of 'gap' in our nanowires can only be explained by considering 'pinned' collective state [3] where pinning strength increases with decreasing diameter. This is consistent with the fact that observed voltage required for switching transition also increases with decreasing diameter. In a previous study existence of collective behavior has been predicted in these nanowires as a non-Curie type temperature dependence of static dielectric constant [15] was observed. Here dipoles (formed by dopant counter ion)

interact among each other via Coulomb interaction and produce a collective pinning [3]. The observed characteristics of V_G here is consistent with Wigner crystal formation which is pinned by the impurity [3, 5, 6].

Above the voltage V_G , I-V characteristics of all nanowires show power law behavior – a known characteristics of 1D conductors. In contrast to conventional three-dimensional (3D) materials, 1D conductors exhibit fascinating transport properties due to the power law dependence of tunneling density of states, which can be parameterized as $dI=dV / T$ and $/ V$ for low bias ($V < k_B T = e$) and high bias ($V > k_B T = e$) conditions respectively [9]. In Fig. 2 (a) we have shown a representative data that show R / T behavior. In this figure we have also plotted the same data as $\log(R)$ vs. $T^{-1/4}$ to show that variable range hopping (VRH) can also give reasonable fit. We found that for low bias data VRH give better fit [15] but power law gives better fit for the data taken with higher bias, as discussed earlier [19]. In the inset of Fig. 2 (a) we have plotted resistivity data (taken with bias 1V) against temperature in log-log scale for 30nm diameter nanowire and fitted it to show that power law dependence (R / T^α , with $\alpha = 5.2$) remains above 30K. Due to the presence of V_G , below 30K the resistance for this bias becomes nearly temperature independent as observed in other polymer nanowires [20]. For 30 nm diameter nanowire taking $\alpha = 5.2$ and plotting $I=T^{1+\alpha}$ versus $eV=(k_B T)$, various I-V curves of different temperatures collapse on a master curve (Fig. 2 (b)). Clean LL state predicts $\alpha = 1$ and scaling of I-V curves of different temperatures to such a master curve [10, 11, 21]. But for the higher diameter nanowires the I-V characteristics of different temperatures could not be collapsed to a single master curve. Presence of V_G , absence of single master curve and unequal exponents (discussed below) and α in these wires show that LL theory is not applicable.

The power law behavior is a characteristic feature of 1D transport [2, 9, 10, 11, 12, 13, 22, 23] and has also been observed in nanowires of conventional CDW materials [24]. From the I-V data we get $\alpha = 5.6$ at $T = 3$ K for 30 nm diameter nanowire (refer upper inset of Fig. 2 (b)) and for other diameter nanowires this value goes up to 7.2 at 3K (refer lower inset of Fig. 2 (b)). Similar power law behavior have been observed in other 1D systems like carbon nanotubes ($\alpha = 0.36$) [10] and nanowires of InSb ($\alpha = 2.7$; $\alpha = 6.13$], polymer ($\alpha = 2.2$ – 7.2 ; $\alpha = 5.7$ – 7.0], NbSe₃ ($\alpha = 1.3$; $\alpha = 1.7$ – 2.7 [24] and MoSe ($\alpha = 0.6$ – 6.6 ; $\alpha = 0.32$ – 4.9 [25]). Although we obtained α' for most of the nanowires at low temperature but the α values were found to decrease with increasing temperature

and with decreasing diameter (refer lower inset of Fig. 2 (b)) – as a result remains unequal to r_s , in general for our wires.

For a quasi-1D system strength of Coulomb correlation is defined as $r_s = a/(2a_B)$, where a is the average distance between electrons and a_B is the effective Bohr radius. Low doped Polymer nanowires with quasi-1D nature and low electron density ($r_s \gg 1$) are a potential candidate to form Wigner crystal that can exhibit characteristics of a charge density wave state [2, 3, 14, 20, 26]. For weakly pinned Wigner crystals tunneling density of states show a power law behavior with the applied bias [22] and the exponent ranges from 3 to 6 [23, 27]. It has been shown [23] that for 1DW C with increasing pinning strength should decrease. The variation of V_G with d (refer inset of 1 (b)) clearly indicates that pinning strength increases [17] with decreasing diameter. Hence our observation of reduction in value with decreasing diameter of nanowires is consistent with 1DW C model. Moreover higher values of the exponents observed here also indicate that 1DW C has formed in our nanowires.

At low temperature all the nanowires show a switching transition to a highly conducting state above a certain threshold voltage $V_{Th} (> V_G)$. We did not observe any switching transition when the bias voltage is kept 1 mV below V_{Th} for long time. The sharp threshold indicates a collective phenomena [28, 29, 30] and the transition is not due to self heating. In Fig. 3(a) and in its inset we have shown representative switching transitions for the nanowires measured at 2.5 K. All the nanowires showed hysteresis in the switching transition which is independent of the bias scan speed (thus removes any possibility of capacitive effect). The nanowires could switch back to the low conducting state only when the applied voltage is reduced to a value V_{Re} ($|V_{Th}| > |V_{Re}| > |V_G|$). With decreasing temperature the hysteresis, defined as $(E_{Th} - E_{Re}) = E_{Re}$ (E_{Re} is the field corresponding to V_{Re}), increases (refer Fig.3 (b)) – this behavior is consistent with that observed in switching CDW [28, 29, 30, 31]. It has been shown theoretically that formation of 1DW C is equivalent to have $4k_F$ CDW in a system [2, 3]. The sliding state of this pinned CDW can explain the field induced switching transition observed here. Presence of V_G and V_{Th} is also consistent with two threshold observed in semiconducting CDW systems [31].

Depending upon the pinning strength a pinned CDW become non-conducting below a certain threshold field. When an applied DC field is strong enough to overcome the pinning energy the CDW depins and sliding motion starts giving rise to a switching transition [28,

29, 30, 31]. When CDW is confined in two direction as in the nanowires, phase deformations occur along the length of the nanowires. In this situation pinning of CDW is one dimensional and the threshold field is expected to be proportional to $d^{-4/3}$ [32]. The plot of E_{Th} vs. d shown in Fig. 3(c) confirms this dependence in our nanowires. The change in E_{Th} with d is obviously not due to surface pinning as that would have given us $E_{Th} \propto d^{-1}$. It has been also observed previously in a study of $NbSe_3$ samples that surface pinning can be excluded for highly resistive samples ($R=L > 1 \text{ m}$) [32]. We measured current-driven I-V characteristics to investigate the nature of switched state in these nanowires. The measurements (Fig. 3(d) and its upper inset) exhibit negative differential resistance (NDR). This type of behavior has been observed in sliding CDW state [31, 33] and is expected in 1D WC. The comparison between voltage driven and current driven I-V characteristics has been shown in Fig. 3(d) and this shows the uniqueness of threshold field for both type of measurements. We have also observed a large fluctuation in the measured voltage in the switched state (refer lower inset of Fig. 3(d)), which gives strong evidence of sliding motion above E_{Th} [31], similar increase in 'noise' has been observed previously in two dimensional Wigner crystal [4].

The results presented here show that the I-V characteristics of all the nanowires have three distinct regions (refer Fig. 3(a)). Below V_G current is very small and that increases with temperature and diameter. Between V_G and V_{Th} power-law characteristics of 1D transport is observed. Above V_{Th} switching transition is observed that exhibit hysteresis, $d^{-4/3}$ scaling, NDR and 'noise' enhancement. All these findings confirm the formation of 1D WC which is expected to exhibit characteristics of CDW, in our nanowire. Although power law dependent I-V characteristics can be explained by other models like Luttinger liquid [9] and environmental Coulomb blockade (ECB) [34], these theories cannot explain the observed switching transition and related phenomena reported here. Moreover, LL theory is clearly inconsistent with observed V_G and reduction of ρ with decreasing diameter (refer inset of Fig. 2(b)). In addition we could not get expected collapse to a master curve [21] for higher diameter nanowires as observed in 30nm wires (refer Fig. 2(b)). ECB theory can account for V_G but it predicts an increase in ρ with increasing environmental impedance but in our case though resistance of the nanowires decreases with increasing diameter - ρ increases. In conclusion all our experimental findings show that one dimensional Wigner crystal has been formed in nanowires of a structurally disordered material like conducting polymer.

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Figure Captions

Fig.1.(a) Differential conductance (dI/dV) is plotted as a function of bias voltage (V) for 30 nm diameter nanowire at various temperatures. Schematic diagram of the two-probe measurement configuration is shown in the inset. (b) Conductance vs. voltage plot for four different diameter nanowires at $T = 3K$. Gap voltage (V_G) for 30nm diameter nanowire has been indicated by an arrow. V_G has been plotted as a function of inverse diameter (d) in the inset.

Fig.2.(a) Resistance (R) vs. temperature (T) data for 50 nm diameter nanowire. Upper arrow indicates plot of $\log_{10} R$ as a function of $T^{-1/4}$ and its linear fit. Lower arrow indicates a double-logarithmic plot of R as a function of T and its fit by a power law $R(T) / T^{-5}$. Power law dependence of R / T data for 30nm diameter nanowire has been shown in the inset. (b) $I = T^{1+\alpha}$ is plotted against $eV = k_B T$, where $\alpha = 5.2$ for 30 nm nanowire for four different temperatures. I-V data for 30 nm diameter nanowire at $T = 3K$ is plotted in a double logarithmic scale in the upper inset. The data is fitted (solid line) by the power law $I / V^{1+\alpha}$ with $\alpha = 5.6$. Plot of α determined at $T = 3K$ is shown as a function of diameter d in lower inset (continuous lines are guide to eye).

Fig.3.(a) Voltage biased I-V characteristics of 110nm diameter nanowire at $T = 2.5K$ showing the gap and switching transition, same for various diameter nanowires are shown in the inset.

(b) Hysteresis ($E_{Th} - E_{Re}$)= E_{Re} is plotted against temperature for 70 nm diameter nanowire. Upper and lower inset shows voltage driven I-V characteristics of 110 and 350 nm diameter nanowires respectively at 2.5K, arrows indicates direction of voltage scan. (c) Threshold field (E_{Th}) is plotted as a function of diameter (symbol) for various nanowires at 2.5 K. The data is fitted (solid line) by the power law E_{Th} / d with $-4/3$. (d) Comparison between voltage biased (square) and current biased (circle) I-V measurements of 450nm diameter nanowire at 1.7K (arrows indicate the direction of scan). In lower inset fluctuations in the voltage has been shown for 3mA (upper curve) and 4mA (lower curve) bias current respectively (note the different scales used). Upper inset shows NDR in the switched state (indicated by (b)).















